

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	635469	(light near emitting near (diode or device or element)) or LED or (laser near diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 17:02
L2	1465	III-V near3 semiconductor near substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 17:05
L3	201	II-VI near3 semiconductor near substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 17:05
L4	4090	(buffer near layer) with (GaN or (gallium near nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 17:07
L5	8498	(monocrystal\$4 or single-crystal\$4) near silicon near substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 17:11
L6	82	I1 and I2 and I4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 17:13
L7	68	I6 and (GaAs or InAs or GaP or InP)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 17:13
L8	13	I1 and I3 and I4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 17:14
L9	242	I1 and I5 and I4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 17:14
L10	206	I9 and (SiN or "Si.sub.3N.sub.4" or (silicon near nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 17:17

L11	19	I9 and ("Al.sub.2O.sub.3" or (aluminum near oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 17:18
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